

# **SMAG Plastic-Encapsulate Diodes**

# **Super Fast Recovery Rectifier Diode**

#### **Features**

•l<sub>0</sub> 1A

●VRRM 50V-600V

High surge current capability

Glass passivated chip

Polarity: Color band denotes cathode

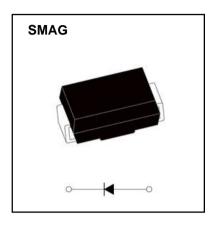
# **Applications**

Rectifier

### Marking

• ES1X

X: From A To J



## **Limiting Values (Absolute Maximum Rating)**

				ES1							
Item	Symbol	Unit	Test Conditions	Α	В	С	D	E	G	Н	J
Repetitive Peak Reverse Voltage	$V_{RRM}$	V		50	100	150	200	300	400	500	600
Maximum RMS Voltage	V <sub>RMS</sub>	٧		35	70	105	140	210	280	350	420
Average Forward Current	I <sub>F(AV)</sub>	Α	60HZ Half-sine wave, Resistance load, $T_L \!\!=\! 120^{\circ}\!$	1.0							
Surge(Non-repetitive)Forward Current	I <sub>FSM</sub>	А	60Hz Half-sine wave ,1 cycle , Ta =25 $^{\circ}\mathrm{C}$								
Junction Temperature	TJ	$^{\circ}$		-55~+150							
Storage Temperature	T <sub>STG</sub>	$^{\circ}\!\mathbb{C}$		-55 ~ <b>+</b> 150							

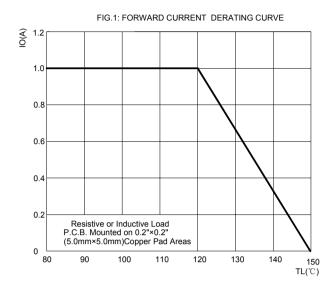
### Electrical Characteristics (T=25°C Unless otherwise specified)

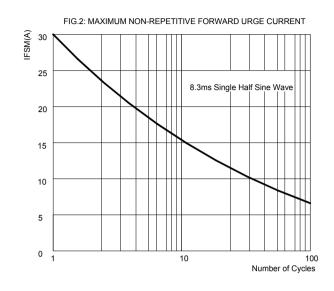
			t Test Condition		ES1									
Item	Symbol	Unit			Α	В	С	D	Е	G	Н	J		
Peak Forward Voltage	V <sub>F</sub>	V	I <sub>F</sub> =1	0.95			1.2	1.25 1.70		.70				
Maximum reverse recovery time	t <sub>rr</sub>	ns	I <sub>F</sub> =0.5A,I <sub>R</sub> =	35										
Peak Reverse Current	I <sub>RRM1</sub>		\/ -\/	T <sub>a</sub> =25℃	5									
Peak Reverse Current	I	μA	V <sub>RM</sub> =V <sub>RRM</sub> T <sub>a</sub> =100°		100									
Thermal	$R_{\theta J-A}$	°C/W	Between junction	85 <sup>1)</sup>										
Resistance(Typical)	$R_{\theta J-L}$	C/VV	Between junction and terminal		35 <sup>1)</sup>									

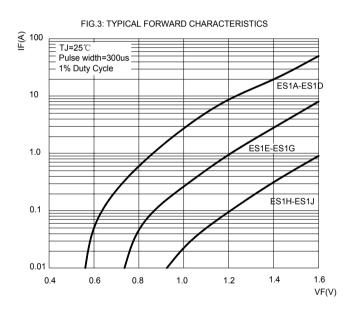
#### Notes:

Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with  $0.2" \times 0.2" (5.0 \text{ mm} \times 5.0 \text{ mm})$  copper pad areas

# **Typical Characteristics**







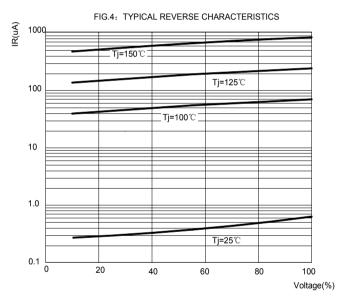
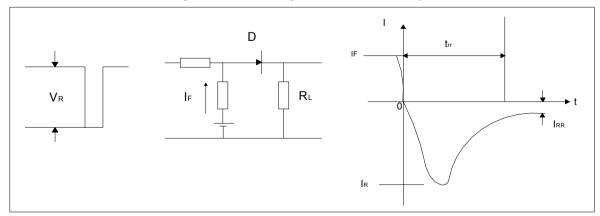
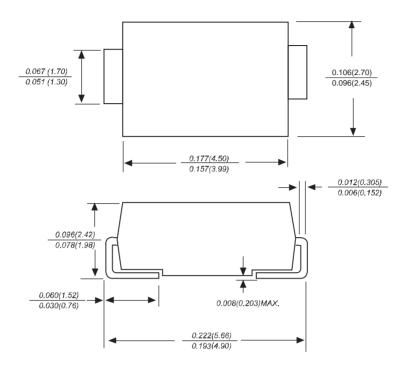


FIG.5: Diagram of circuit and Testing wave form of reverse recovery time

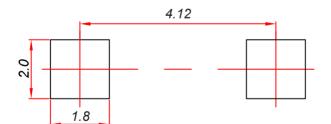


### **SMAG** Package Outline Dimensions



Dimensions in inches and (millimeters)

## **SMAG Suggested Pad Layout**



#### Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance: ± 0.05mm.
- 3. The pad layout is for reference purposes only.

#### NOTICE

JSHD reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. JSHD does not assume any liability arising out of the application or use of any product described herein.

# **Reel Taping Specifications For Surface Mount Devices-SMAG**

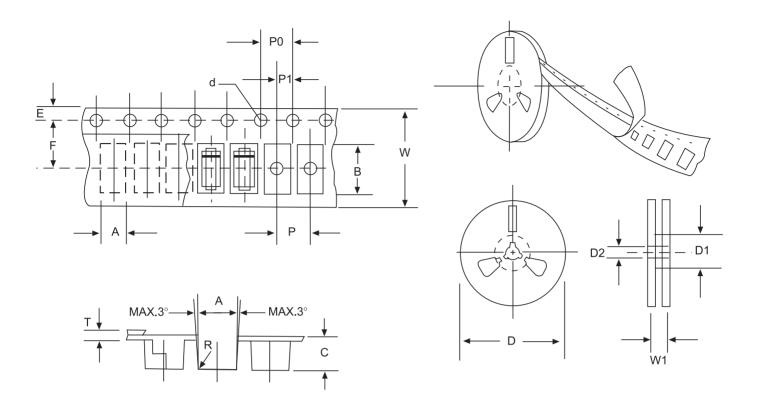


Fig:CONFIGURATION OF FLAT MELF TAPING

ITEM	SYMBOL	SMAG mm(inch)
Carrier width	А	2.79±0.1(0.110±0.004)
Carrier length	В	5.33±0.1(0.210±0.004)
Carrier depth	С	2.36±0.1(0.093±0.004)
Sprocket hole	d	1.5±0.05 (0.059±0.0002)
Reel outside diameter	D	330/178±2.0(13/7.0±0.79)
Reel inner diameter	D1	75/54 ±1.0 (2.95/2.13 ±0.039)
Feed hole diameter	D2	13±0.5(0.512±0.020)
Strocket hole position	E	1.75±0.1(0.069±0.004)
Punch hole position	F	5.5±0.05(0.217±0.002)
Punch hole pitch	Р	4.0±0.1(0.157±0.004)
Sprocket hole pitch	P0	4.0±0.1(0.157±0.004)
Embossment center	P1	2.0±0.1(0.079±0.004)
Totall tape thickness	Т	0.28±0.02(0.011±0.0008)
Tape width	W	12.0±0.2(0.472±0.008)
Reel width	W1	16.8±2.0(0.661±0.079)

NOTE:Devices are packde in accordance with EIA standard RS-481-A and specification given above.